NO. :



APPROVAL SHEET

MULTILAYER CERAMIC CAPACITOR

Automotive Grade (AEC-Q200 Qualified)

Approved by customer : (signing or stamping here)

SAM	WHA CAPACITOR CO	D., LTD.
Prepared by	Checked by	Approved by
2485	for	74

2020. 02. 28.

SAMWHA CAPACITOR CO., LTD.

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< SPECIFICATION SUMMARY >										
SAMWHA Part no.		CQ	3216X7R225K500NRI							
Туре	1	*MLCC fo	or Automotive Application							
Items	Specification	Unit	Test Conditions							
Capacitance	2.2	μF	_ Testing Frequency : 1 ±0.1 kHz							
Capacitance Tolerance	± 10	%	Testing Voltage : 1 ±0.2 Vrms							
Dissipation Factor	Max. 12.5	%	Should be measured at 25 °C.							
Insulation Resistance	Min. 22.7	MΩ	Should be measured with a DC voltage not exceeding rated voltage at 25 °C for 2 minutes of charging.							
	3.20 ±0.30	L (mm)	Capacitance Tolerance Code page 1/9							
Chip Size	1.60 ±0.20	W (mm)	Chip size page 2/9							
	1.60 ±0.20	T (mm)	Characteristics & Test Method page 3/9~6/9							
	*Thin Lay	ver Large-Ca	apacitance Type							

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Enactment: Feb. 1, 2010	MULTILAYER CERAMIC CAPACITOR Automotive Grade							Pa	age		1 / 9	
1. General Code												
(1) Type Designation												
<u>CQ</u> (1)	<u>32</u> ′ (2			2 25 (4)	<u>K</u> (5)	<u>500</u> (6)	<u>N</u> (7)	<u>R</u> (8)	<u> </u> (9))		
1) Multilayer Ceram	ic Cap	acitor (Au	tomoti	ve Gra	ade)							
Tł	e first	xpressed two digits					t two	digits	are wi	dth.		
3) Temperature Co Classification		Code		Т	empera	ature R	ange		Сара	citance	e Tolera	ance
Class		COG				o +125	-		oupu	±30 p		
		X7R			-55 to +125℃				±1			
Class		X7S			-55 t	o +125	C		±22%			
Class II		X7T			-55 to +125℃ -55 to +105℃				+22% ~ -33%			
The first two dig ex) 104 = 1000 R denotes 0 8R2 = 8.2	00 _p F decimal		gnifica	nt figu	ires ar	nd the	last c	igit de	enotes	the n	umber	ot zero
5) Capacitance Tol	erance	Code										
Code		Tolera	nce				Code			Tole	rance	
В		± 0.1	pF				G			± 2	.0 %	
С		± 0.25					J				5 %	
D F		± 0.5 ± 1.0					K M				0 % 20 %	
6) Voltage Code		<u> </u>			I	L		1		<u> </u>		
	100 1	60 250	350	500	101	201	251	501	631	102	202	302
0000 0100		DC DC	DC	DC	DC	DC	DC	DC	DC	DC	DC	DC
Rated DC	1	6V 25V	35V	50V	100V	200V	250V	500V		1KV	2KV	3KV
	10V 1	201										
	e late		minati	on Tyj	be							

9) Thickness option

Thickne	ess (mm)	Cada	Thickne	ss (mm)	Code	
t	Tolerance(±)	Code	t	Tolerance(±)	Code	
0.50	0.05	Blank	1.35	0.20	Н	
0.60	0.10	A	1.60	0.20	l	
0.80	0.10	В	1.80	0.20	J	
0.85	0.15	В	2.00	0.25	К	
1.00	0.15	E	2.50	0.25	L	
1.10	0.15	E	2.80	0.30	М	
1.15	0.15	E	3.20	0.30	Ν	
1.25	0.15	E	5.00	0.40	0	
1.30	0.20	E				

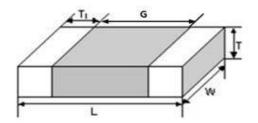
*3216 Size \geq 2.2 μ F 100V \Rightarrow T : Tol±0.30

2. Temperature Characteristics

See Page 6/9 (No.21)

3. Constructions and Dimensions

(1) Dimensions



		Dimension									
Size Code	EIA Code	Length		Wi	dth	T4(min)					
		L	Tol(±)	W	Tol(±)	T1(min.)	G(min.)				
1005	0402	1.00	0.05	0.50	0.05	0.05	0.30				
1608	0603	1.60	0.15	0.80	0.10	0.10	0.50				
2012	0805	2.00	0.20	1.25	0.15	0.10	0.65				
3216	1206	3.20	0.30	1.60	0.20	0.15	1.00				
3225	1210	3.20	0.40	2.50	0.25	0.15	1.05				
4520	1808	4.50	0.40	2.00	0.25	0.20	1.50				
4532	1812	4.50	0.40	3.20	0.30	0.20	1.50				
5750	2220	5.70	0.50	5.00	0.40	0.30	1.85				

*3216 Size \geq 2.2 μ F 100V \Rightarrow L, W : Tol±0.30

(2) Construction of Termination



(Unit : mm)

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Specifications and Test Methods (For Automotive Applications)

No.	AEC-	Q200	Spec	cification	Test Methods and Conditions				
NO.	Test	ltem	Class I	Class II					
1	Pre-and Post- Electrical Test			-	-				
		Appearance	No defects which may affect	performance					
2	High Temperature Exposure	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger) $30pF$ min.: Q \geq 1000	− Temperature : Max. operating temperature±3℃ Maintenance Time : 1000+48/-0 hrs					
	(Storage)	Q/D.F.	30pF max.: Q≧400+20×C C: Nominal Capacitance (pF)	10V: 0.075 max. *0.2 max.	Let sit for 24±2 hours at room temperature, then measure.				
		I.R.	More than 10,000M Ω or 500 Ω (Whichever is smaller)	₽F (*50Ω·F)					
		Appearance	No defects which may affect	performance	Perform the 1000 cycles according to the four heat treatments				
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	Within ±10.0%	listed in the following table. Let sit for 24±2 hours at room temperature, then measure.				
3	Temperature		30pF min.:Q≧1000	Rated Voltage 16V min.: 0.05 max.	Step 1 2 3 4 Tume (%) 55.0(.0) 65.0 405.0(.0) 65.0				
Ũ	Cycle	Q/D.F.	30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	10V: 0.075 max. *0.2 max.	Temp.(°C) -55+0/-3 25±2 125+3/-0 25±2 Time(min) 15±3 1 15±3 1				
		I.R.	More than 10,000MΩ or 500Ω (Whichever is smaller)	₽F (*50Ω·F)	Initial measurement Perform the initial measurement according to Note 1 for Cla				
4	Destructive Physical Anal	ysis	No defects or abnormalities		Per EIA-469				
		Appearance	No defects which may affect	performance	Temperature : 25~65°C, Humidity : 80~98%				
	5 Moisture	Capacitance Change	Within ±3.0% or±0.30pF (Whichever is larger)	Within ±12.5%	Cycle Time : 24 hrs/cycle, 10 cycles Let sit for 24±2 hours at room temperature, then measure.				
5		Q/D.F.	30pF min.: $Q \ge 350$ 10pF min. and 30pF max.: $Q \ge 275+5/2xC$ 10pF max.: $Q \ge 200+10xC$ C: Nominal Capacitance (pF)	Rated Voltage 16V min.: 0.05 max. 10V: 0.075 max. *0.2 max.	70 ← 90-98%/RH → ← KH → 60 55 50 50 50 50 50 50 5				
		I.R.	More than 10,000MΩ or 500Ω (Whichever is smaller)	₽F (*50Ω·F)	15 10 5 0 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 Time (hrs)				
		Appearance	No defects which may affect	performance	_				
		Capacitance Change	Within ±3.0% or ±0.30pF (Whichever is larger)	Within ±12.5%	Temperature : 85±3 °C Humidity : 80~85%				
6	Biased Humidity	Q/D.F.	30pF min.: Q≧200 30pF max.: Q≧100+10/3×C C: Nominal Capacitance (pF)	Rated Voltage 16V min.: 0.05 max. 10V: 0.075 max. *0.2 max.	Applied Voltage : Rated Voltage and 1.3+0.2/-0V Maintenance Time : 1000+48/-0 hrs Let sit for 24±2 hours at room temperature, then measure.				
		I.R.	More than 1,000M Ω or 50 Ω ·F (Whichever is smaller)	(*5Ω·F)	The charge/discharge current is less than 50mA.				
		Appearance	No defects which may affect	performance					
		Capacitance Change	Within ±3.0% or ±0.30pF (Whichever is larger)	Within ±12.5%	- Temperature : Max. operating temperature±3℃ Applied Voltage : Rated Voltage × 200% (*150%) Maintenance Time : 1000+48/-0 hrs				
7	Operational Life	Q/D.F.	30pF min.:Q \geq 350 10pF min. and 30pF max.: Q \geq 275+5/2xC 10pF max.: Q \geq 200+10xC C: Nominal Capacitance (pF)	Rated Voltage 16V min.: 0.05 max. 10V: 0.075 max. *0.2 max.	Let sit for 24±2 hours at room temperature, then measure. The charge/discharge current is less than 50mA. Initial Measurement for Class II Applied 200% of the rated voltage for one hour at 125±3°C. Remove and let sit for 24±2 hours at room temperature, then				
		I.R.	More than 1,000M Ω or 50 Ω ·F (Whichever is smaller)	(*5Ω·F)	measure.				

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No.		-Q200	Speci	fication	Test Methods and Conditions
	Test	ltem	Class I	Class II	
8	External Visu	al	No defects or abnormalities		Visual inspection
9	Physical Dime	ension	Within the specified dimensions		Using calipers
		Appearance	No defects which may affect ;	performance	
		Capacitance Change	Within the specified tolerance		
10	Resistance to Solvents Q/D.F.		30pF min.: Q≧1000 30pF max.: Q≧400+20xC C: Nominal Capacitance (pF)	Rated Voltage 50V: 0.025 max. 25V: 0.03 max. 16V: 0.035 max. 10V: 0.05 max. *0.125 max.	Per MIL-STD-202 Method 215
		I.R.	More than 10,000M Ω or 500 Ω f (Whichever is smaller)		
		Appearance	No defects which may affect p	performance	
		Capacitance Change	Within the specified tolerance		Three shocks in each direction should be applied along 3 mutually perpendicular axes of the test specimen (18 shocks)
11	Mechanical Shock	Q/D.F.	30pF min.:Q≧1000 30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	Rated Voltage 50V: 0.025 max. 25V: 0.03 max. 16V: 0.035 max. 10V: 0.05 max. *0.125 max.	Test Pulse Wave form : Half-sine Duration : 0.5ms Peak value : 1,500G
		I.R.	More than 10,000M Ω or 500 Ω -f (Whichever is smaller)		Velocity change : 4.7m/s
		Appearance	No defects or abnormalities		
		Capacitance Change	Within the specified tolerance		The specimens should be subjected to a simple harmonic motion
12	2 Vibration Q/D.F.		30pF min.:Q≧1000 30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	Rated Voltage 50V: 0.025 max. 25V: 0.03 max. 16V: 0.035 max. 10V: 0.05 max.	having a total amplitude of 1.5mm. The entire frequency range of 10 to 2,000 Hz and return to 10 Hz should be traversed in 20 minutes. This cycle should be performed 12 times in each of three mutually perpendicular directions (total of 36 times).
		I.R.	More than 10,000MΩ or 500Ω-f (Whichever is smaller)	*0.125 max. = (*50Ω·F)	-
		Appearance	No defects which may affect p	performance	
		Capacitance Change	Within the specified tolerance	1	Temperature (Eutectic solder solution) : 260 ± 5 °C
13	Resistance to Soldering Heat	Q/D.F.	30pF min.:Q≧1000 30pF max.:Q≧400+20×C C: Nominal Capacitance (pF)	Rated Voltage 50V: 0.025 max. 25V: 0.03 max. 16V: 0.035 max. 10V: 0.05 max.	Dipping Time : 10±1s Let sit for 24±2 hours at room temperature, then measure. Initial measurement
		I.R.	More than 10,000MΩ or 500Ωł (Whichever is smaller)	*0.125 max. = (*50Ω·F)	Perform the initial measurement according to Note 1 for Class II.
		Appearance	No defects which may affect p	performance	Perform the 300 cycles according to the two heat treatments listed
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	Within ±15.0%	in the following table. Transfer Time : 20sec. max.
14	Thermal Shock	Q/D.F.	30pF min.:Q≧1000 30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	Rated Voltage 50V: 0.025 max. 25V: 0.03 max. 16V: 0.035 max. 10V: 0.05 max.	Let sit for 24 ± 2 hours at room temperature, then measure.Step1Temp.(°C)-55+0/-3125+3/-0Time(min)15+3
		I.R.	More than 10,000MΩ or 500Ωf (Whichever is smaller)	*0.125 max.	Time(min.) 15±3 15±3 Initial measurement Perform the initial measurement according to Note 1 for Class II.

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Specifications and Test Methods (For Automotive Application)

	AEC-0	Q200	Specif	fication		Test Matheda and Canditiana				
No.	Test		Class	Class	П	Test Methods and Conditions				
		Appearance Capacitance	No defects which may affect pe Within the specified tolerance	erformance		-				
15	ESD	Change Q/D.F.	30pF min.:Q≧1000 30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	16V:	0.025 max. 0.03 max. 0.035 max. 0.05 max.	Per AEC-Q200-002				
		I.R.	More than 10,000M Ω or 500 Ω ·F	(*50Ω·F)						
16	Solderability		(Whichever is smaller) 95% of the terminations is to be s	oldered evenly and c	ontinuously.	 (a) Preheat at 155 °C for 4 hours, and then immerse the capacitor in a solution of ethanol and rosin. Immerse in eutectic solder solution for 5+0/-0.5 seconds at 235±5 °C. (b) Steam aging for 8 hours, and then immerse the capacitor in a solution of ethanol and rosin. Immerse in eutectic solder solution for 5+0/-0.5 seconds at 235±5 °C. (c) Steam aging for 8 hours, and then immerse the capacitor in a solution of ethanol and rosin. Immerse in eutectic solder solution of ethanol and rosin. Immerse in eutectic solder solution of ethanol and rosin. Immerse in eutectic solder solution of ethanol and rosin. Immerse in eutectic solder solution of ethanol and rosin. Immerse in eutectic solder solution for 120±5 seconds at 260±5 °C. 				
		Appearance	No defects or abnormalities			The capacitance/Q/D.F. should be measured at 25 °C at the				
		Capacitance Change	Within the specified tolerance			Class Capacitance CC Frequency Voltage Class Capacitance (C) Frequency Voltage Class Capacitance (C) Frequency Voltage Class Capacitance (C) Frequency Voltage				
Electrical 17 Characteriza- tion		Q/D.F.	30pF min.:Q≧1000 30pF max.:Q≧400+20xC C: Nominal Capacitance (pF)	16V:	0.025 max. 0.03 max. 0.035 max. 0.05 max.	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$				
		I.R. at 25℃	More than 100,000M Ω or 1,000 $\Omega\cdot F$ (Whichever is smaller)	More than 10,000M (*50Ω·F) (Whicheve		Should be measured with a DC voltage not exceeding rated				
		I.R. at 125℃	More than 10,000M Ω or 100 Ω ·F (Whichever is smaller)	More than 1,000MΩ (*1Ω·F) (Whichever		voltage at 25 $^\circ\!\!\!\mathrm{C}$ and 125 $^\circ\!\!\!\mathrm{C}$ for 2 minutes of charging.				
		Dielectric Strength	No dielectric breakdown or mecha	anical breakdown		Applied 250% of the rated voltage for 1~5 seconds The charge/discharge current is less than 50mA.				
			No defects which may affect pe	erformance		Apply a force in the direction shown in the following figure for 60±5 seconds.				
18	Board Flex	Capacitance Change	Within ±5.0% or ±0.5pF (Whichever is larger)	Within the specified	tolerance	45±2 45±2 Probe to exert bending force Speed: 1.0mm/s Printed circuit board under test Flexure for Class I: 3mm max.				
	Tamain I	Appearance	No defects which may affect pe	l erformance		for Class II: 2mm max. Apply 18N ¹⁾ force in parallel with the test jig for 60±1 seconds.				
19	Terminal Strength	Capacitance	Within ±5.0% or ±0.5pF	Within the specified	toloropoo	¹⁾ 10N for 1608(EIA:0603) size				

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	ecificatio	-Q200		Specification T Class Class									Τ
No.		Item	Class					Test Methods and Conditions					
			The chip endure following force.			Apply a force			0 0				
			Chip Length Thickness		ess (T)	Force	(i) Chip Lengtl Beam Spe		`	ii) Chip Le	ngth : 3.2 peed : 2.5		
			2.5mm max.	T≤0.5	ōmm	8N	Beam Spe	eu . 0.5m	11/5	Deam 3	peed . z.:	51111/5	
20	Beam Load T	est	2.511111 11187.	T>0.5	ōmm	20N							
			3.2mm min.	T<1.2	5mm	15N	0	lro	on Board				
			3.2000 000	T≥1	.25	54.5N					0.6		
			-		_						* *		
		Capacitance Change			X7R : Wit X7S : Wit X6S : Wit X7T : Wit	nin ±22%	measured in s sequentially fr	The temperature coefficient is determined using the capacitance measured in step 3 as a reference. When cycling the temperature sequentially from step 1 through 5, the capacitance should be					
21	Capacitance Temperature	Temperature Coefficient	0±30 ppm/℃				within the spe The capacitan between the n 1, 3 and 5 by	ice drift is naximum	calculated and minim	l by dividin um measu	g the diffe ired value	erences	
21	Characteris-						Step	1	2	3	4	5	
	tics						Temp.(℃)	25±2	-55±3	25±2	125±3	25±2	
		Capacitance Drift	Within ±0.2% or ±0.05 (Whichever is larger)	ōpF			(ii) Class II The ranges of over the temp Initial measure Perform the in	erature ra ement	inge from -	55℃ to 12	5℃.		

In the case of "*" is specifications for "Thin Layer Large Capacitance Type"

Note 1. Initial Measurement for Class II

Perform a heat treatment at 150+0/-10 °C for one hour, and then let sit for 24±2 hours at room temperature, then measure.

SW - Q - 01A	
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Packing

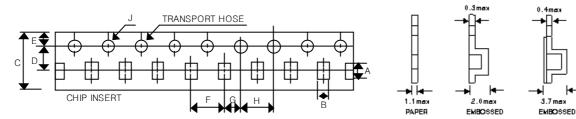
- (1) Bulk Packing
 - 1 1000 pcs per polybag
 - 2 5 polybags per inner box
 - 3 10 inner boxes per out box
- (2) Reel Packing
 - (1) 8~10 reels per inner box
 - 2 6 inner boxes per out box
- (3) Reel Dimensions

E	Π								(Ui	nit : mm)
	L I_	Mark	Size Code	EIA Code	Α	В	С	D	Е	w
\Q1/î	ſ <u>I</u>	7 " Reel	1005~3225	0402~1210	Ф 178±2	Ф 50Min	Ф13±0.5	Ф 21±0.8	2±0.5	10±1.5
\setminus \square			4520~4532	1808~1812	Ф180+0,-3	Ф60-0,+1	Φ13±0.2	Φ57-0+1	3±0.2	13±0.5
$\sim \rightarrow$	U w U 	13 " Reel	1005~3225	0402~1210	Ф 330±2	Ф70Min	Ф13±0.5	Ф21±0.8	2±0.5	10±1.5

(4) Number of Package

Size Code	EIA Code	7"	13"		
		Quantity(pcs)/Reel	Quantity(pcs)/Reel		
1005	0402	10,000	50,000		
1608	0603	4,000	15,000		
2012	0805	3,000 ~ 4,000	8,000 ~ 15,000		
3216	1206	2,000 ~ 4,000	6,000 ~ 10,000		
3225	1210	1,000 ~ 3,000	4,000 ~ 10,000		
4520	1808	1,500 ~ 3,000	_		
4532	1812	500 ~ 1,000	1,500 ~ 5,000		

(5) Tape Dimensions



Size Code	EIA Code	А	В	С	D	E	F	G	н	J
1005	0402	1.15±0.1	0.65±0.1	8.0±0.3	3.5±0.05	1.75±0.1	2.0±0.05	2.0±0.1	4.0±0.1	1.5±0.1
1608	0603	1.9±0.2	1.10±0.2	8.0±0.3	3.5±0.05	1.75±0.1	4.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1
2012	0805	2.4±0.2	1.65±0.2	8.0±0.3	3.5±0.05	1.75±0.1	4.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1
3216	1206	3.6±0.2	2.00±0.2	8.0±0.3	3.5±0.05	1.75±0.1	4.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1
3225	1210	3.6±0.2	2.80±0.2	8.0±0.3	3.5±0.05	1.75±0.1	4.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1
4520	1808	4.8±0.2	2.3±0.2	12.0±0.3	5.5±0.1	1.75±0.1	4.0±0.1 8.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1
4532	1812	4.9±0.2	3.6±0.2	12.0±0.3	5.5±0.1	1.75±0.1	8.0±0.1	2.0±0.1	4.0±0.1	1.5±0.1

BLAN K	CHIPS	BLA	NK	LEADER
10 to 20pitch	•	20 to 4	0pitch	200 to 250mm
•••••••••••••	•••	+ ⊕⊕⊕⊕⊕	\$\$	¢
			-0 0 0]
DRA	WING DIRECTION			

		SW - Q - 01A 8 / 9			
aution					
 Storage Condition When solderability is considered (1) Temperature: 25°C ± 10°C (2) Relative Humidity: Below 7 		ded to be used in 12 months.			
 The Regulation of Environment Never use materials mentioned Pb, Cd, Hg, Cr⁺⁶, PBB(Polybrock) 	d below in MLCC products	regulated this document. olybrominated diphenyl ethers), asbestos			
Mounting Position Choose a mounting position the imposed on the chip during flee board.		[Component direction] ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓			
		[Chip Mounting Close to Board Separation Point]			
 The sudden temperature changes damages to ceramic componer procedures should be required components. Please refer to the recommend shown in figures, and keep the within the range recommended Table 1 	hts. Therefore, the preheating for the soldering of ceramic ed soldering profiles as temperature difference(\triangle T)	Recommended Reflow Soldering Profile for Lead Free Solder Infrared Reflow Temperature 250±10°C 200°C 160±10°C 140±10°C Preheating			
Size code (EIA Code)	Temperature Difference				
1005~3216 (0402~1206)	∆T≤190 ℃	60~120 sec. 30~60 sec.			
3225 (1210)	∆T≤130 ℃	Vapor Reflow Temperature			
		250±10°C 160±10°C 140±10°C Preheating 60~120 sec. 20 sec. max.			

	SW - Q - 01A	9/9
Note		
'Aging'/'De-aging' behavior of high dielectric constant type MLCCs		

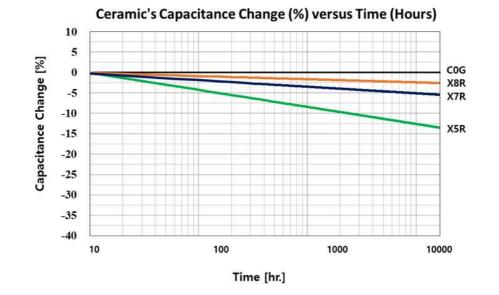
(Typically represented by X7R temperature characteristic of which main composition is BaTiO₃)

'Aging' / 'De-aging' Behavior of high dielectric MLCCs Please note that high dielectric type dielectric ceramic capacitors have a "normal" 'aging' behavior / characteristic, that is; their capacitance value decreases with time from its value when it was first manufactured. From that date, the capacitance value begins to decrease at a logarithmic rate defined by:

$C_t = C_{24} (1 - k \log 10 t)$

where,

- $C_t\;$: Capacitance value, t hours after the start of 'aging'
- $C_{\rm 24}$: Capacitance value, 24 hours after its manufacture
- k : Aging constant (capacitance decrease per decade-hour)
- t : time, in hours, from the start of 'aging'



The capacitance value can be restored (also known as 'de-aged') by exposing the component to elevated temperatures approaching its curie temperature (approximately 120°C). This 'de-aging' can occur during the component's solder-assembly onto the PCB, during life or temperature cycle testing, or by baking at 150°C for about 1 hour.